Phase Leg IGBT 7 Power Module

APTGX75A170T1G

Product Overview

The APTGX75A170T1G device is a phase leg 1700V, 75A Insulated-Gate Bipolar Transistor (IGBT) 7 power module.

The following figures show the electrical diagram and pinout location of the device.

Figure 1. Electrical Diagram

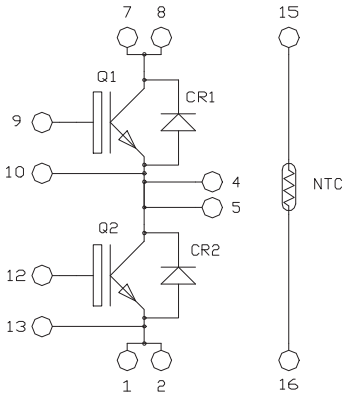
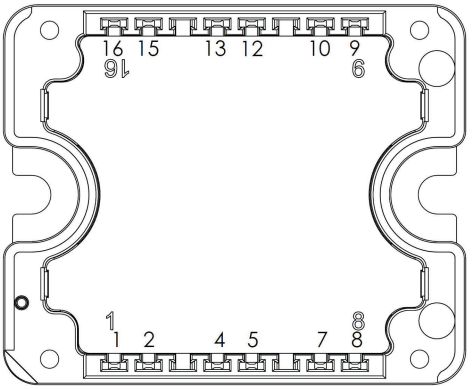


Figure 2. Pinout Location



Notes:

- Pins 7/8, 4/5, and 1/2 must be shorted together.
- All ratings are at T_J = 25 °C, unless otherwise specified.

CAUTION These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The APTGX75A170T1G device has the following key features:

- IGBT 7
  - Low-voltage drop
  - Low-leakage current
- Very low-stray inductance
- Kelvin emitter for easy drive
- Internal thermistor for temperature monitoring
- Al_2O_3 substrate and copper base plate

Benefits

The APTGX75A170T1G device has the following benefits:

- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

Potential Applications

The APTGX75A170T1G device has the following potential applications:

- Welding converters
- Switched-mode power supplies
- Uninterruptible power supplies
- Electric Vehicle (EV) motor and traction drive

1. Electrical Specifications

The following sections show the electrical specifications of the APTGX75A170T1G device.

1.1 IGBT Characteristics (Per IGBT)

The following table lists the absolute maximum ratings (per IGBT) of the APTGX75A170T1G device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
V_{CES}	Collector-emitter voltage		1700	V
I_C	Continuous collector current	T_C = 25 °C	120	A
		T_C = 100 °C	75	
I_{CM}	Pulsed collector current, t_P limited by $T_{J(max)}$		150	
V_{GE}	Gate-emitter voltage		±20	V
P_D	Power dissipation	T_C = 25 °C	382	W

The following table lists the electrical characteristics (per IGBT) of the APTGX75A170T1G device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
I_{CES}	Zero gate voltage collector current	V_{GE} = 0V; V_{CE} = 1700V		—	—	10	µA
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15V I_C = 75A	T_J = 25 °C	—	1.7	2	V
			T_J = 125 °C	—	1.95	—	
			T_J = 175 °C	—	2.1	—	
$V_{GE(th)}$	Gate threshold voltage	V_{GE} = V_{CE}; I_C = 1.54 mA		5.15	5.8	6.45	
I_{GES}	Gate-emitter leakage current	V_{GE} = 20V; V_{CE} = 0V		—	—	150	nA

The following table lists the dynamic characteristics (per IGBT) of the APTGX75A170T1G device.

Table 1-3. Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	V_{GE} = 0V V_{CE} = 25V f = 100 kHz		—	7.6	—	nF
C_{oes}	Output capacitance			—	0.13	—	
C_{res}	Reverse transfer capacitance			—	0.03	—	
Q_G	Gate charge	V_{GE} = ±15V V_{CE} = 900V I_C = 75A		—	0.72	—	µC
$T_{d(on)}$	Turn-on delay time	V_{GE} = ±15V V_{Bus} = 600V I_C = 75A R_G = 4.7Ω	T_J = 25 °C	—	110	—	ns
			T_J = 125 °C	—	120	—	
			T_J = 175 °C	—	130	—	
T_r	Rise time		T_J = 25 °C	—	25	—	
			T_J = 125 °C	—	30	—	
			T_J = 175 °C	—	34	—	
$T_{d(off)}$	Turn-off delay time		T_J = 25 °C	—	341	—	
			T_J = 125 °C	—	438	—	
			T_J = 175 °C	—	483	—	
T_f	Fall time		T_J = 25 °C	—	200	—	
			T_J = 125 °C	—	350	—	
			T_J = 175 °C	—	500	—	
E_{on}	Turn-on energy	V_{GE} = ±15V V_{Bus} = 900V I_C = 75A R_G = 4.7Ω di/dt = 1700 A/µs dv/dt = 4500 V/µs	T_J = 25 °C	—	9.4	—	mJ
			T_J = 125 °C	—	16.5	—	
			T_J = 175 °C	—	20.5	—	
E_{off}	Turn-off energy		T_J = 25 °C	—	12.4	—	
			T_J = 125 °C	—	19.8	—	
			T_J = 175 °C	—	23.8	—	
R_{Gint}	Internal gate resistance			—	2.9	—	Ω
I_{sc}	Short circuit data	V_{GE} ≤ 15V V_{Bus} = 1000V t_P ≤ 8 µs	T_J = 150 °C	—	290	—	A
		V_{GE} ≤ 15V V_{Bus} = 1000V t_P ≤ 7 µs	T_J = 175 °C	—	280	—	
R_{thJC}	Junction-to-case thermal resistance			—	—	0.392	°C/W

1.2 Diode Characteristics (Per Diode)

The following table lists the diode characteristics (per diode) of the APTGX75A170T1G device.

Table 1-4. Diode Characteristics

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
V_{RRM}	Peak repetitive reverse voltage			—	—	1700	V
I_{RM}	Reverse leakage current	V_R = 1700V		—	—	10	µA
I_{FRM}	Repetitive forward current, t_P limited by $T_{J(max)}$			—	150	—	A
I^2t	I^2t value	t_p = 10 ms V_R = 0V	T_J = 125 °C	—	1150	—	A^2s
			T_J = 175 °C	—	740	—	
I_F	DC forward current	T_C = 65 °C	T_J = 175 °C	—	75	—	A
V_F	Diode forward voltage	I_F = 75A V_{GE} = 0V	T_J = 25 °C	—	2.35	2.7	V
			T_J = 125 °C	—	2.25	—	
			T_J = 175 °C	—	2.1	—	
I_{RRM}	Reverse recovery current	V_{GE} = –15V I_F = 75A V_R = 900V di/dt = 1700 A/µs	T_J = 25 °C	—	110.6	—	A
			T_J = 125 °C	—	118.6	—	
			T_J = 175 °C	—	120	—	
Q_{rr}	Reverse recovery charge		T_J = 25 °C	—	10.3	—	µC
			T_J = 125 °C	—	19.1	—	
			T_J = 175 °C	—	25.1	—	
E_{rr}	Reverse recovery energy		T_J = 25 °C	—	5.4	—	mJ
			T_J = 125 °C	—	11	—	
			T_J = 175 °C	—	14.8	—	
R_{thJC}	Junction-to-case thermal resistance			—	—	0.613	°C/W

1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the APTGX75A170T1G device.

Table 1-5. Thermal and Package Characteristics

Symbol	Characteristic			Min.	Typ.	Max.	Unit
V_{ISOL}	RMS isolation voltage, any terminal-to-case t = 1 min, 50/60 Hz			4000	—	—	V
L_{stray}	Stray inductance module			—	16	—	nH
d_{creep}	Creepage distance terminal-to-heatsink			—	13.4	—	mm
d_{clear}	Clearance distance terminal-to-heatsink			—	12.8	—	
R_{CE}	Lead resistance terminal-to-chip	T_C = 25 °C, per switch		—	1.8	—	mΩ
T_J	Operating junction temperature range			–40	—	175	°C
T_{STG}	Storage temperature range			–40	—	125	
T_C	Operating case temperature			–40	—	125	
τ_M	Mounting torque	To heatsink	M4	2	—	3	N.m
Wt	Package weight			—	66	—	g

The following table lists the temperature sensor NTC of the APTGX75A170T1G device.

Table 1-6. Temperature Sensor NTC

Symbol	Characteristic		Min.	Typ.	Max.	Unit
R_{25}	Resistance at 25 °C		—	50	—	kΩ
$\Delta R_{25}/R_{25}$	—		—	5	—	%
$B_{25/85}$	T_{25} = 298.15K		—	3952	—	K
ΔB/B	—	T_C = 100 °C	—	4	—	%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

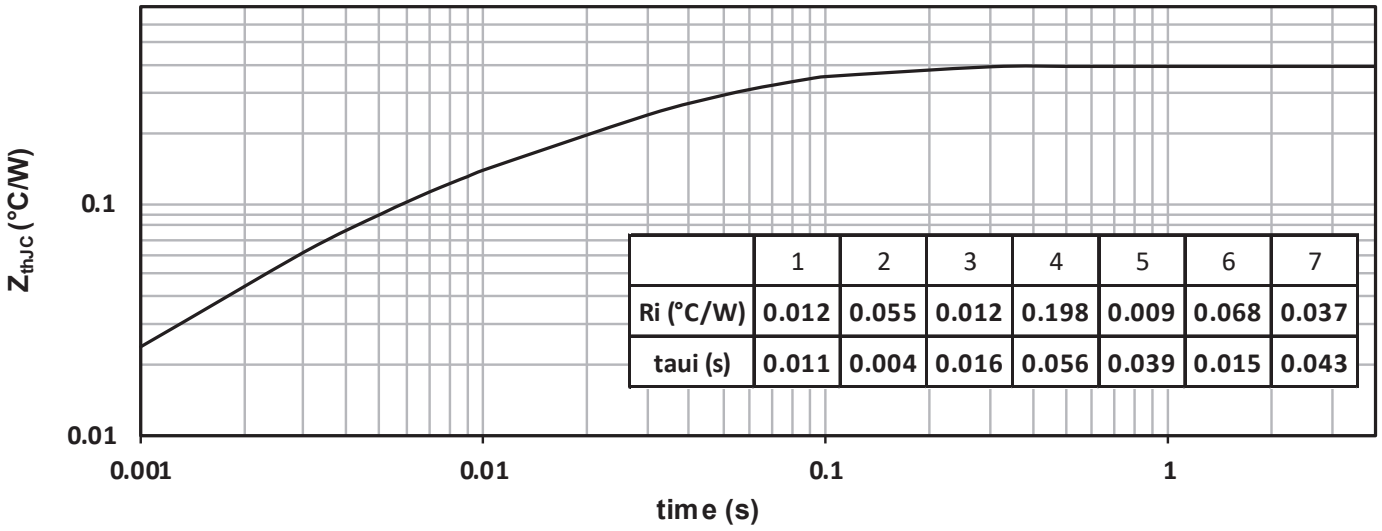
T: Thermistor temperature
R_T: Thermistor value at T

Note: For more information, see APT0406—Using NTC Temperature Sensor Integrated into Power Module.

1.4 Typical IGBT Performance Curve

The following figures show the IGBT performance curves of the APTGX75A170T1G device.

Figure 1-1. Maximum Thermal Impedance



	1	2	3	4	5	6	7
Ri (°C/W)	0.012	0.055	0.012	0.198	0.009	0.068	0.037
taui (s)	0.011	0.004	0.016	0.056	0.039	0.015	0.043

Figure 1-2. Output Characteristics, V_{GE} = 15V

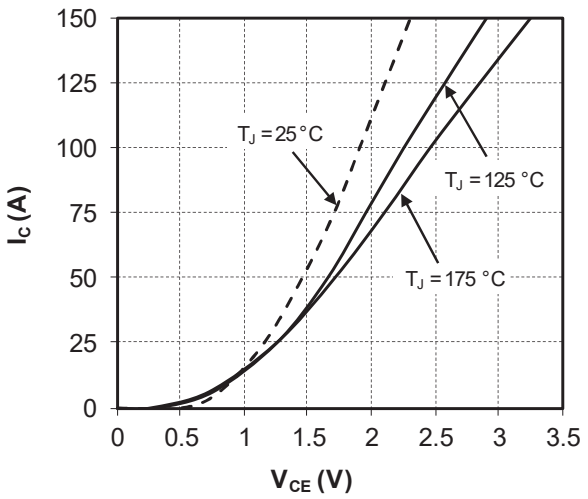


Figure 1-3. Output Characteristics, T_J = 175 °C

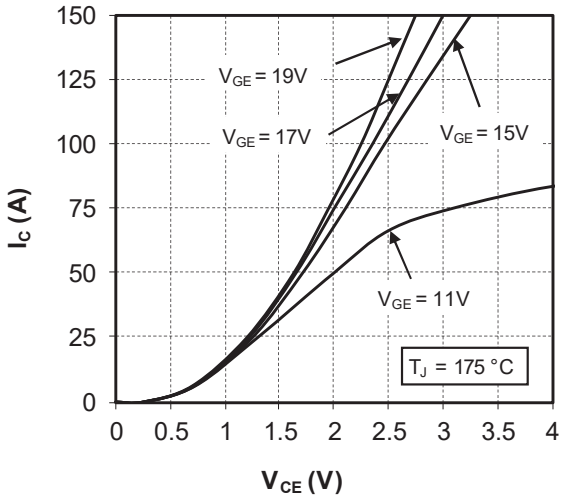


Figure 1-4. Switching Losses vs. Gate Resistance

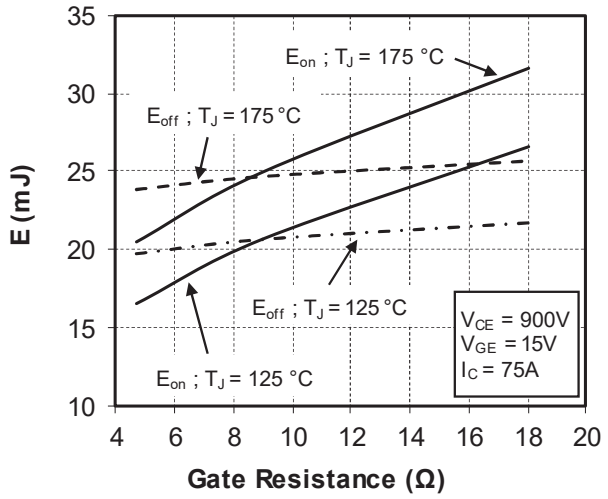


Figure 1-5. Switching Losses vs. Collector Current

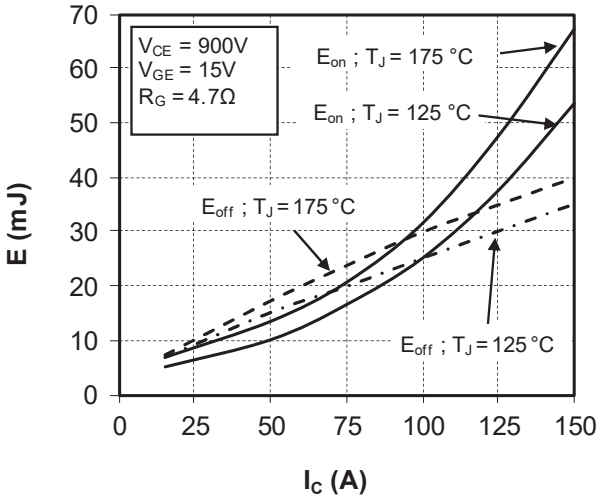


Figure 1-6. Operating Frequency vs. Collector Current

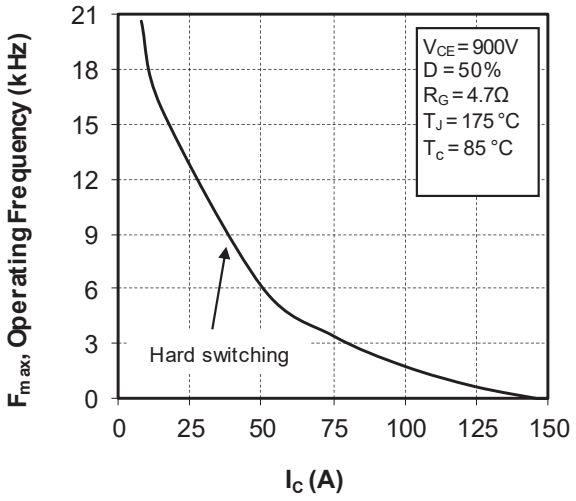


Figure 1-7. Gate Charge Characteristics

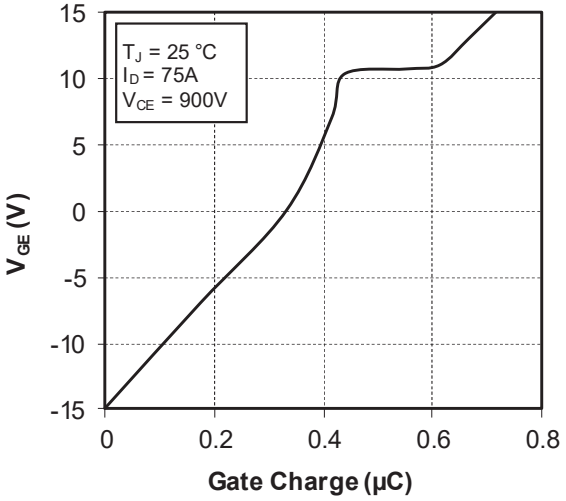


Figure 1-8. Transfer Characteristics

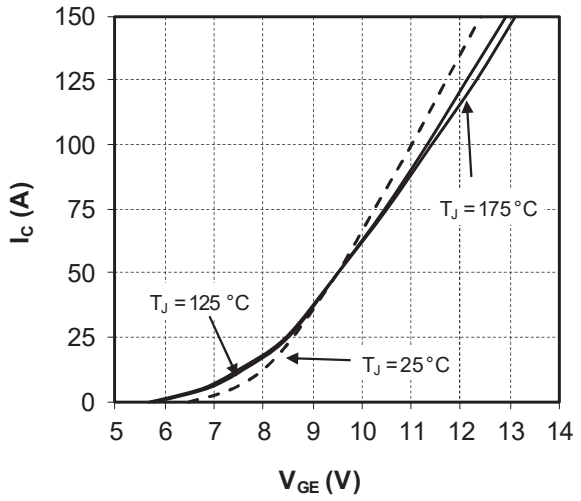


Figure 1-9. Capacity Characteristics

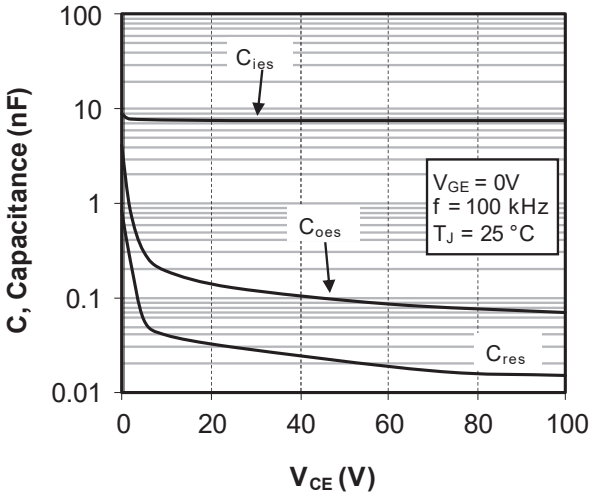
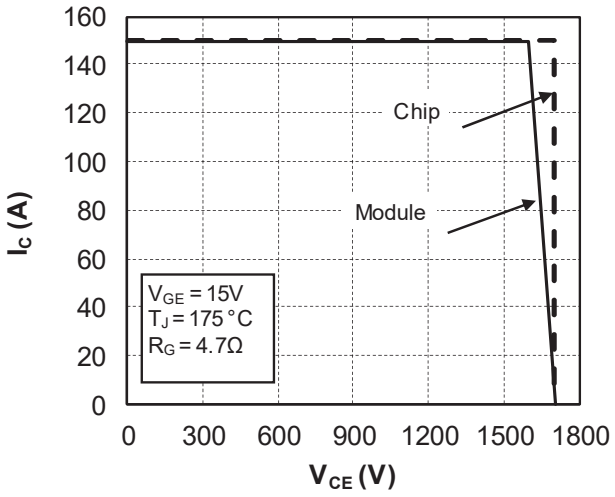


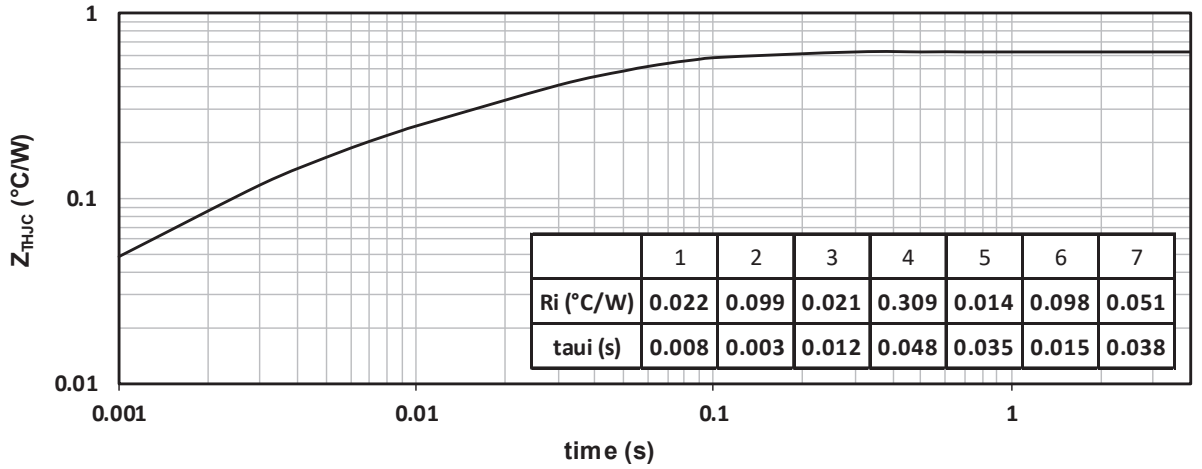
Figure 1-10. Reverse Bias Safe Operating Area



1.5 Typical Diode Performance Curve

The following figures show the diode performance curves of the APTGX75A170T1G device.

Figure 1-11. Maximum Thermal Impedance



	1	2	3	4	5	6	7
Ri (°C/W)	0.022	0.099	0.021	0.309	0.014	0.098	0.051
taui (s)	0.008	0.003	0.012	0.048	0.035	0.015	0.038

Figure 1-12. Forward Characteristics

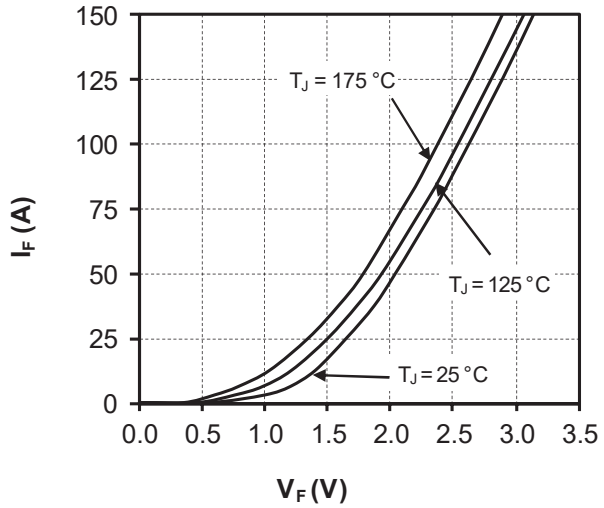


Figure 1-13. Switching Losses vs. Gate Resistance

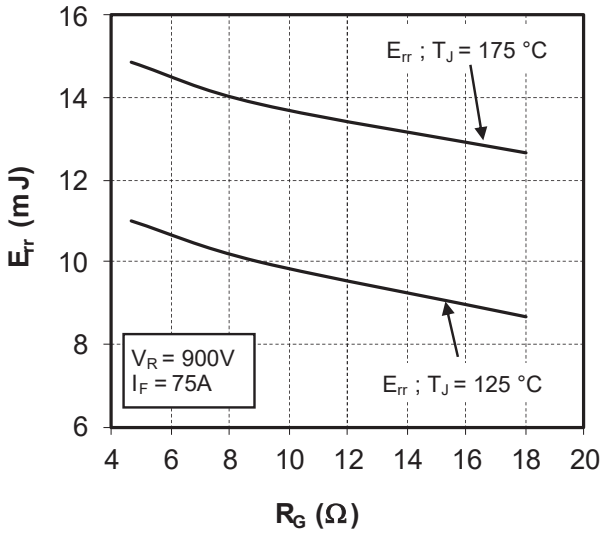
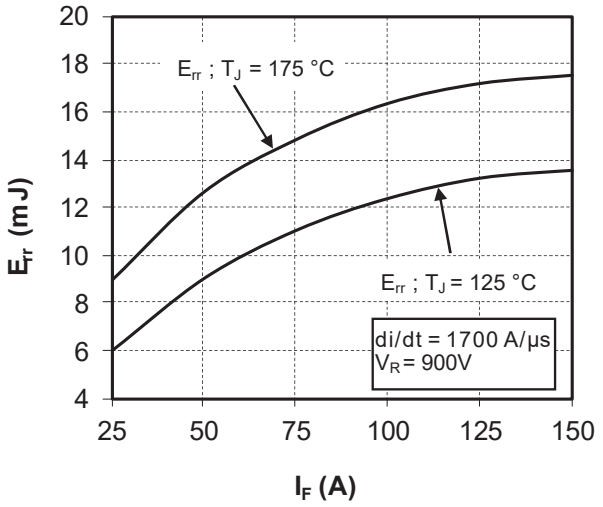


Figure 1-14. Switching Losses vs. Forward Current



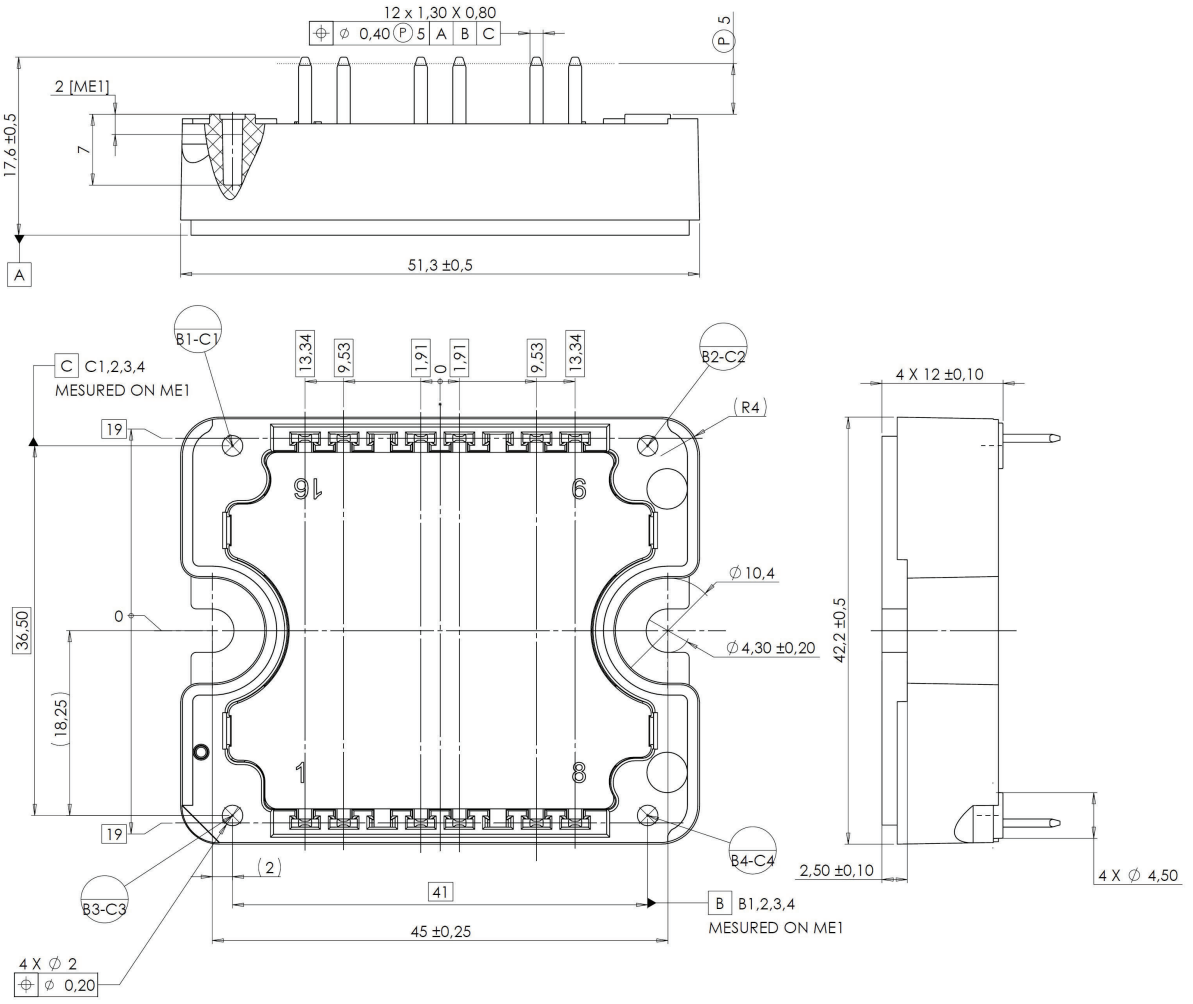
2. Package Specifications

The following section shows the package specification of the APTGX75A170T1G device.

2.1 Package Outline

The following figure shows the package outline drawing of the APTGX75A170T1G device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: For more information, see AN3500A-Mounting instructions for SP1F and SP3F power modules.

3. Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Revision	Date	Description
A	11/2024	Initial revision

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